

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (Ta=25°C)					電 氣 的 特 性 (Ta=25°C)										外 形	備 考	
				V _{CEO} (V)	V _{ESO} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CB} (V)	直流又はパルス h _{FE}		バイアス		h _{FE}	h _{ie}	h _{ie} *	h _{FE} *			h _{oe}
1	2	3	4	5					6		7		8				9	10		11	12

- 1** TYPE NUMBER
- 2** ORIGINAL MANUFACTURER
- 3** USES
- 4** MATERIAL AND STRUCTURE
- 5** MAXIMUM RATINGS
- 6** I_{CEO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CEO})
- 7** STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8** STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9** f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T.
 - 10** C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11** OUTLINE
 - 12** REMARKS
- : とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 ($T_a = 25^\circ\text{C}$)					電 気 的 特 性 ($T_a = 25^\circ\text{C}$)											外形	備考		
				V_{CBO} (V)	V_{EBO} (V)	I_C (mA)	P_C (mW)	T_j ($^\circ\text{C}$)	I_{CBO} 最大値		直流又はパルス h_{FE}		バイアス		h_{fe} h_{fb}^*	h_{ie} h_{ib}^* (Ω)	h_{re} h_{rb}^* ($\times 10^{-4}$)	h_{oe} h_{ob}^* (μV)	$f_{\beta b}$ f_T^* (Mc)			C_{ob} (pF)	$r_{bb'}$ $h_{ie}(\text{real})^*$ (Ω)
									(μA)	$V_{CB}(\text{V})$	$V_{CE}(\text{V})$	$I_C(\text{mA})$	$V_{CB}(\text{V})$	$I_E(\text{mA})$									
★ 2SC1451	富士通	RF	Si.EP	150	5	50	700	175	1	140	150	5	10	5	-10	$t_{on} < 1\mu\text{S}, t_{off} < 10\mu\text{S}$ $t_{sig} < 9.5\mu\text{S}$	130*	2	70*	248			
★ "	"	"	"	150	5	50	700	175	1	140	150	5	10	5	-10	$t_{on} < 1\mu\text{S}, t_{off} < 10\mu\text{S}$ $t_{sig} < 9.5\mu\text{S}$	130*	2	70*	248			
★ "	東芝	"	"	55	5	100	200	150	0.1	30	120	1	10	10	-1		150*	5	20	195			
"	サンケン	PA	Si.TMe	300	6	4A	50W ($T_c=25^\circ\text{C}$)	150	1mA	300	>20	5	1A	12	-100		10*			102			
"	1455																						
★ "	日電	PA	Si.TP	300	7	200	15W ($T_c=25^\circ\text{C}$)	150	0.1	200	80	10	10	30	-10		80*	3.8	30	99			
"	1457	RF	Si.E	35	3	150	800	200	0.1	20	100	10	50	10	-50	$NF < 3.2\text{dB}$ ($f=200\text{MHz}, V_{CE}=10\text{V}, I_C=20\text{mA}$)	2700*	C_{rc} 1	45*	85B			
"	1458	"	"	20	3	50	300	200	0.1	10	100	5	30	5	-15	$ S_{21e} ^2 = 9\text{dB}$ ($f=1\text{GHz}$)	3000*	C_{re} 0.9	30*	130			
"	1459	富士通	Si.EP	15	3	70	300	175	0.5	10	80	6	40	6	-40		5000*	1	25*	199			
"	1460	"	"	15	3	30	250	175	0.5	10	80	6	10	6	-10	$NF=4.5\text{dB}$ ($f=2\text{GHz}, V_{CE}=6\text{V}, I_C=4\text{mA}$)	4500*	0.7	25*	199			
"	1461	"	"	15	3	40	250	175	0.5	10	80	6	20	6	-20		4500*	0.8	25*	199			
"	1462	"	"	15	3	30	250	175	0.5	10	80	6	15	6	-15	$NF=3.5\text{dB}$ ($f=2\text{GHz}, V_{CE}=6\text{V}, I_C=4\text{mA}$)	6500*	0.7	25*	199			
"	1463	SW	Si.T	450	5	4A	75W ($T_c=25^\circ\text{C}$)	175	10	150	18	5	1A	6	-300	$t_r < 5\mu\text{S}, t_f < 3\mu\text{S}$ $t_{sig} < 5\mu\text{S}$	25*	125	5*	102			
"	1464	PA	Si.EP	50	3.5	500	4W ($T_c=25^\circ\text{C}$)	175	250	20	80	5	200	12	-100	$P_o=1.2\text{W}$ ($f=175\text{MHz}, V_{cc}=12\text{V}, P_i=50\text{mW}$)	1300*	3.5		84C			
"	1465	"	"	50	3.5	500	7W ($T_c=25^\circ\text{C}$)	175	250	20	80	5	200	12	-100	$P_o=1.8\text{W}, \eta=55\%$ ($f=0.7\text{GHz}, V_{cc}=24\text{V}, P_i=0.3\text{W}$)	1600*	4.5		231			
"	1466	新電元	Si.DB	450	4	3A	30W ($T_c=25^\circ\text{C}$)	150	1mA	450	16	5	1.5A	10	1A	$t_{on} < 2\mu\text{S}, t_f < 2\mu\text{S}$ $t_{sig} < 4\mu\text{S}$	10*	60		204			
"	1467	"	"	500	4	3A	30W ($T_c=25^\circ\text{C}$)	150	1mA	500	12	5	1.5A	10	1A		10*	60		204			
"	1468	"	"	450	4	10A	100W ($T_c=25^\circ\text{C}$)	150	10mA	450	16	5	5A	10	1A		10*	300		102			
"	1469	"	"	500	4	10A	100W ($T_c=25^\circ\text{C}$)	150	10mA	500	12	5	5A	10	2A		10*	300		102			
"	1470	"	"	450	4	30A	200W ($T_c=25^\circ\text{C}$)	150	10mA	450	16	5	10A	10	2A		10*	700		266			
"	1471	"	"	500	4	30A	200W ($T_c=25^\circ\text{C}$)	150	10mA	500	12	5	10A	10	2A		10*	700		266			
"	1472	日立	Si.EP	40	10	300	500	125	0.1	30	2000~ 100000	5	10	5	-10	$t_{on}=60\text{nS}, t_{off}=800\text{nS}$ $t_{sig}=350\text{nS}$	>50*	<10	220	138			
"	1473	松下	PA	250	5	70	600	125	2	12	120	10	5	10	-10		80*	5	$C_c r_{bb'}$ 60pS	138			
"	1474	ソニー	RF.PA	16	6	2A	750	120	0.2	16	300	2	100	2	-10		60*	30	$C_c r_{bb'}$ 600pS	259	2SA772 とコンプリ		
"	1475	"	"	100	6	1A	750	120	0.2	25	300	2	100	2	-10		80*	16	$C_c r_{bb'}$ 300pS	259	2SA773 とコンプリ		
★ "	東芝	PA	Si.EP	38		5A	40W ($T_c=25^\circ\text{C}$)	175	1mA	15	50	5	1A			$P_o=28\text{W}$ ($f=470\text{MHz}, V_{cc}=12.6\text{V}, P_i=12\text{W}$)				135			
"	1477	サンケン	SW	230	6	9A	80W ($T_c=25^\circ\text{C}$)	150	1mA	230	20	4	5A			$t_r < 1.5\mu\text{S}, t_f < 1\mu\text{S}$ $t_{sig} < 4\mu\text{S}$				102			
"	1478	松下	RF.LN	35	5	50	150	175	0.1	10	540	5	2	5	-2	5500	0.4	25	150*	2.2	70	243	
"	1479	富士通	PA	36	3.5	500	3W ($T_c=25^\circ\text{C}$)	175	100	12	50	2	200	12	-100	$P_o=1.2\text{W}$ ($f=175\text{MHz}, V_{cc}=12.5\text{V}, P_i=50\text{mW}$)	1000*	4		84B			
★ "	1480	"	"	36	3.5	500	7W ($T_c=25^\circ\text{C}$)	175	100	12	50	2	500	12	-100	$P_o=2.4\text{W}, \eta=60\%$ ($f=470\text{MHz}, V_{cc}=12.5\text{V}, P_i=0.3\text{W}$)	1200*	5		246			